SHANGHAI SUNRISE ELECTRONICS CO., LTD.

ESTA THRU ESTG SURFACE MOUNT SUPER FAST SWITCHING RECTIFIER VOLTAGE: 50 TO 400V CURRENT: 1.0A

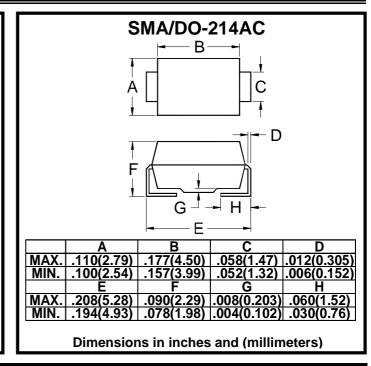
TECHNICAL SPECIFICATION

FEATURES

- Ideal for surface mount pick and
- place application
- Low profile package
- Built-in strain relief
- High surge capability
- Glass passivated chip
- Super fast recovery for high efficiency
- High temperature soldering guaranteed: 260°C/10sec/at terminal

MECHANICAL DATA

- Terminal: Plated leads solderable per MIL-STD 202E, method 208C
- Case: Molded with UL-94 Class V-O
 - recognized flame retardant epoxy
- Polarity: Color band denotes cathode



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(Single-phase, half-wave, 60Hz, resistive or inductive load rating at 25°C, unless otherwise stated, for capacitive load, derate current by 20%)

RATINGS	SYMBOL	ES1A	ES1B	ES1C	ES1D	ES1E	ES1G	UNITS
Maximum Repetitive Peak Reverse Voltage	V _{RRM}	50	100	150	200	300	400	V
Maximum RMS Voltage	V _{RMS}	35	70	105	140	210	280	V
Maximum DC Blocking Voltage	V _{DC}	50	100	150	200	300	400	V
Maximum Average Forward Rectified Current (T _L =110°C)	I _{F(AV)}	1.0						А
Peak Forward Surge Current (8.3ms single half sine-wave superimposed on rated load)	I _{FSM}	30						А
Maximum Instantaneous Forward Voltage (at rated forward current)	V _F	0.95 1.25				V		
Maximum DC Reverse Current $T_a=25^{\circ}C$ (at rated DC blocking voltage) $T_a=100^{\circ}C$		5.0 200						μΑ μΑ
Maximum Reverse Recovery Time (Note 1)	trr	35						nS
Typical Junction Capacitance (Note 2)	CJ	10						pF
Typical Thermal Resistance (Note 3)	R _θ (ja)	40						°C/W
Storage and Operation Junction Temperature	T_{STG},T_{J}	-50 to +150					°C	
Note:								

1. Reverse recovery condition I_F =0.5A, I_R =1.0A, Irr=0.25A.

2.Measured at 1.0 MHz and applied voltage of $4.0V_{\rm dc}$

3. Thermal resistance from junction to terminal mounted on 5×5mm copper pad area

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